



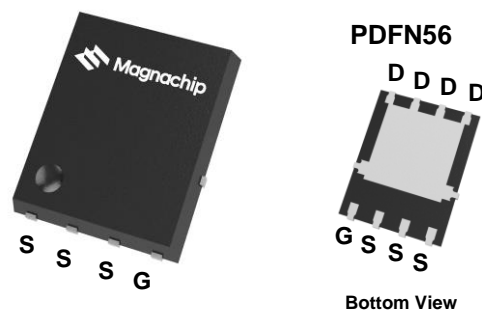
# MDU1051RH

Single N-channel Trench MOSFET 150V 47mΩ 27A

## General description

The MDU1051RH uses advanced Magnachip's MOSFET technology, which provides high performance in on-state resistance, fast switching performance and excellent quality.

These devices can also be utilized in industrial applications such as Synchronous Rectification and general Purpose applications.



Top View

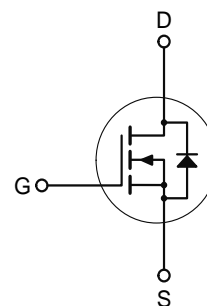
Bottom View

## Features and benefits

- Magnachip's MOSFET Technology
- 100% Avalanche / Rg Tested

## Applications

- Specifically for Synchronous Rectification
- Switching Applications



## Key performance parameters

$V_{DS}$	150	V
$R_{DS(on), max}$	0.047	$\Omega$
$I_D$	27	A
$Q_G$	20.9	nC
Junction temperature <sub>,max</sub>	150	$^{\circ}C$



## Ordering information

Type / Ordering Code	Package	Marking	Packing	RoHS Status
MDU1051RH	PDFN56	MDU1051	Tape & Reel	compliant

<http://www.magnachip.com>

**Maximum ratings**, at  $T_A = 25^\circ\text{C}$ , unless otherwise specified

Parameter		Symbol	Rating	Unit
Drain-source Voltage		$V_{DS}$	150	V
Gate-source Voltage		$V_{GS}$	$\pm 20$	V
Drain current	$T_C=25^\circ\text{C}$	$I_D$	27	A
	$T_C=100^\circ\text{C}$		17	A
<sup>1)</sup> Pulsed drain current	$T_C=25^\circ\text{C}$	$I_{DM}$	108	A
Total power dissipation	$T_C=25^\circ\text{C}$	$P_{tot}$	66	W
	$T_C=100^\circ\text{C}$		26	W
<sup>2)</sup> Avalanche energy, single pulse		$E_{AS}$	50	mJ
Operating and storage temperature		$T_j, T_{stg}$	- 55 ~ 150	$^\circ\text{C}$

**Thermal characteristics**

Parameter		Symbol	Rating	Unit
Thermal resistance, junction - case		$R_{\theta JC}$	1.9	K/W
<sup>3)</sup> Thermal resistance, junction - ambient		$R_{\theta JA}$	50	K/W

**Notes**

- Pulse width limited by  $T_{jmax}$
- Starting  $T_J=25^\circ\text{C}$ ,  $L=1\text{mH}$ ,  $I_{AS}=10\text{A}$ ,  $V_{DD}=50\text{V}$ ,  $V_{GS}=10\text{V}$
- Surface mounted FR-4 board by JEDEC (jesd51-7)

Electrical Characteristics ( $T_J = 25^\circ\text{C}$ )

## Static characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions / Note
Drain-source breakdown voltage	$V_{(BR)DSS}$	150	-	-	V	$V_{GS}=0\text{ V}$ , $I_D=250\ \mu\text{A}$
Gate threshold voltage	$V_{GS(th)}$	1.2	2.2	3.2	V	$V_{DS}=V_{GS}$ , $I_D=250\ \mu\text{A}$
Zero gate voltage drain current	$I_{DSS}$	-	-	1	$\mu\text{A}$	$V_{DS}=120\text{ V}$ , $V_{GS}=0\text{ V}$
Gate-source leakage current	$I_{GSS}$	-	-	$\pm 100$	nA	$V_{GS}=\pm 20\text{ V}$ , $V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	38	47	m $\Omega$	$V_{GS}=10\text{ V}$ , $I_D=20\text{ A}$
Gate resistance	$R_G$	-	1.4	-	$\Omega$	$f=1\text{ MHz}$
Transconductance	$g_{fs}$	-	30	-	S	$V_{DS}=10\text{ V}$ , $I_D=20\text{ A}$

## Dynamic characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions / Note
Input capacitance	$C_{iss}$	-	1,321	-	pF	$V_{GS}=0\text{ V}$ , $V_{DS}=75\text{ V}$ , $f=1\text{ MHz}$
Output capacitance	$C_{oss}$	-	130	-	pF	$V_{GS}=0\text{ V}$ , $V_{DS}=75\text{ V}$ , $f=1\text{ MHz}$
Reverse transfer capacitance	$C_{rss}$	-	13	-	pF	$V_{GS}=0\text{ V}$ , $V_{DS}=75\text{ V}$ , $f=1\text{ MHz}$
Turn-on delay time	$t_{d(on)}$	-	15	-	ns	$V_{DD}=75\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=20\text{ A}$ , $R_{G,ext}=3\Omega$
Rise time	$t_r$	-	4	-	ns	$V_{DD}=75\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=20\text{ A}$ , $R_{G,ext}=3\Omega$
Turn-off delay time	$t_{d(off)}$	-	33	-	ns	$V_{DD}=75\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=20\text{ A}$ , $R_{G,ext}=3\Omega$
Fall time	$t_f$	-	6	-	ns	$V_{DD}=75\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=20\text{ A}$ , $R_{G,ext}=3\Omega$

## Gate charge characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions / Note
Gate to source charge	$Q_{gs}$	-	4.7	-	nC	$V_{DD}=75\text{ V}$ , $I_D=20\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Gate charge at threshold	$Q_{gs(th)}$	-	2.6	-	nC	$V_{DD}=75\text{ V}$ , $I_D=20\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Gate to drain charge	$Q_{gd}$	-	5.3	-	nC	$V_{DD}=75\text{ V}$ , $I_D=20\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Switching charge	$Q_{sw}$	-	7.4	-	nC	$V_{DD}=75\text{ V}$ , $I_D=20\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Gate charge total	$Q_g$	-	20.9	-	nC	$V_{DD}=75\text{ V}$ , $I_D=20\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Gate plateau voltage	$V_{plateau}$	-	3.64	-	V	$V_{DD}=75\text{ V}$ , $I_D=20\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$

## Source-drain diode

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions / Note
Diode continuous forward current	$I_S$	-	-	27	A	-
Diode pulse current	$I_{S,pulse}$	-	-	108	A	pulsed; $t_p \leq 10\ \mu\text{s}$
Diode forward voltage	$V_{SD}$	-	0.9	1.3	V	$V_{GS}=0\text{ V}$ , $I_F=20\text{ A}$
Reverse recovery time	$t_{rr}$	-	97	-	ns	$I_F=20\text{ A}$ , $d_{IF}/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge	$Q_{rr}$	-	282	-	nC	$I_F=20\text{ A}$ , $d_{IF}/dt=100\text{ A}/\mu\text{s}$

Electrical characteristics diagrams

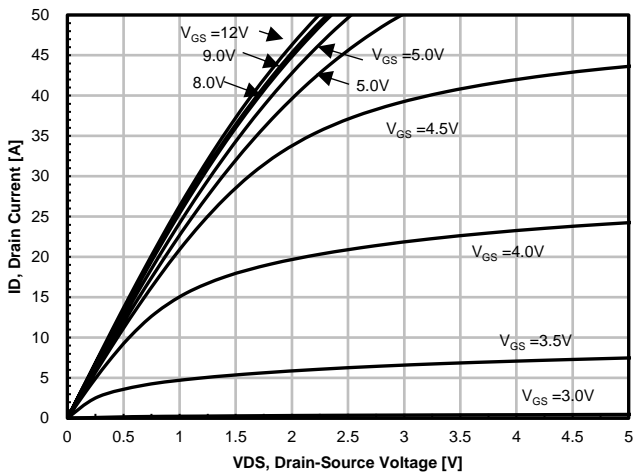


Fig. 1. On-Region Characteristics

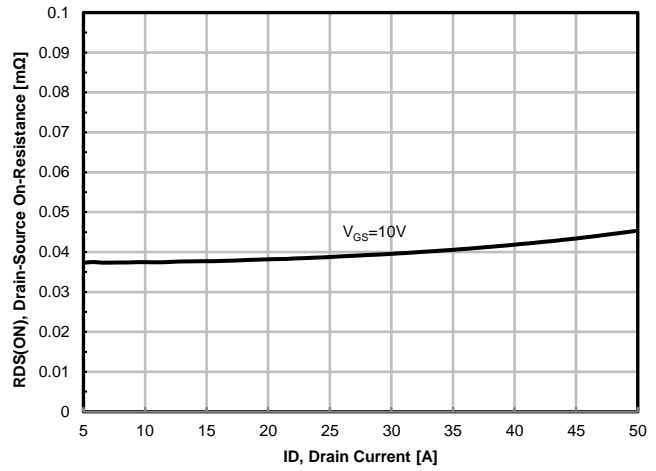


Fig. 2. On-Resistance vs. Drain Current and Gate Voltage

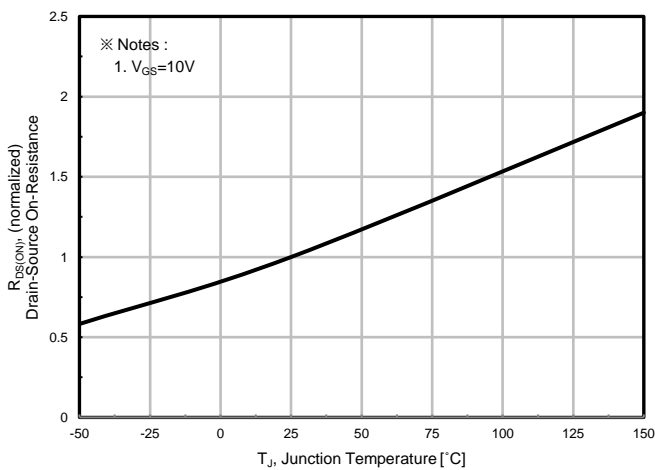


Fig. 3. On-Resistance vs. Junction Temperature

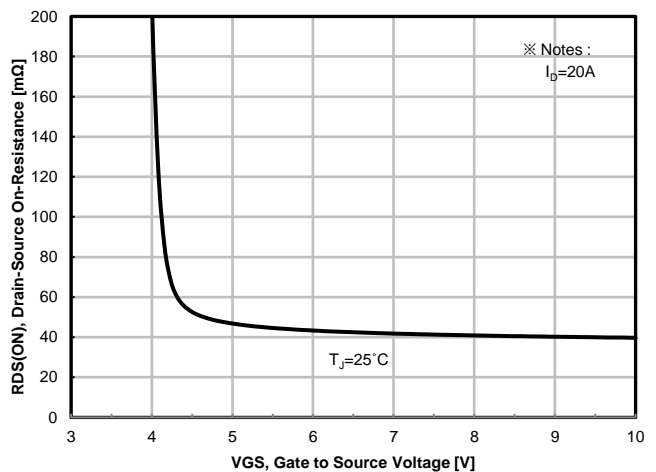


Fig. 4. On-Resistance vs. Gate to Source Voltage

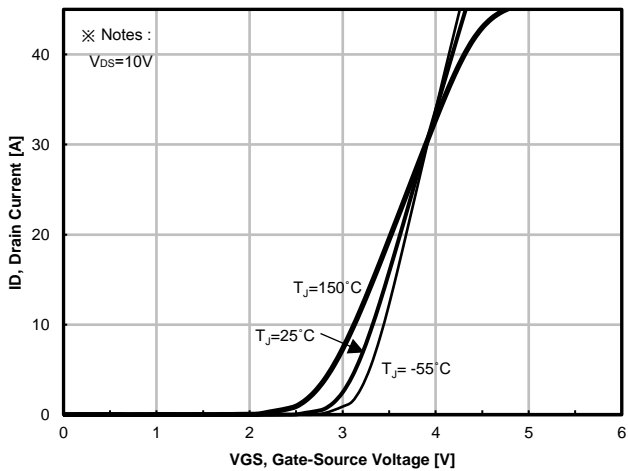


Fig. 5. Transfer Characteristics

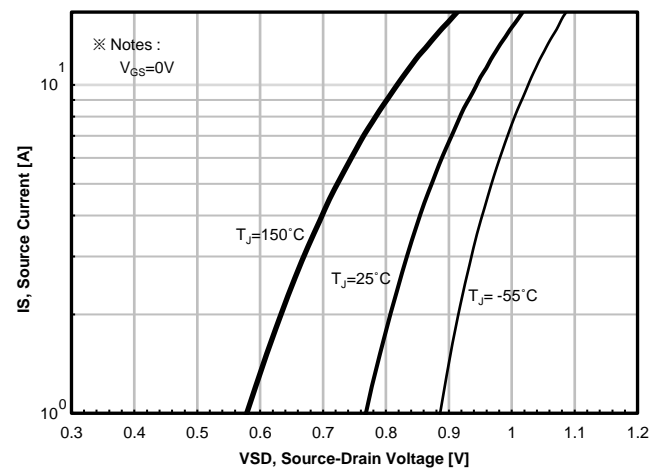


Fig. 6. Source-Drain Diode Forward Voltage

Electrical characteristics diagrams

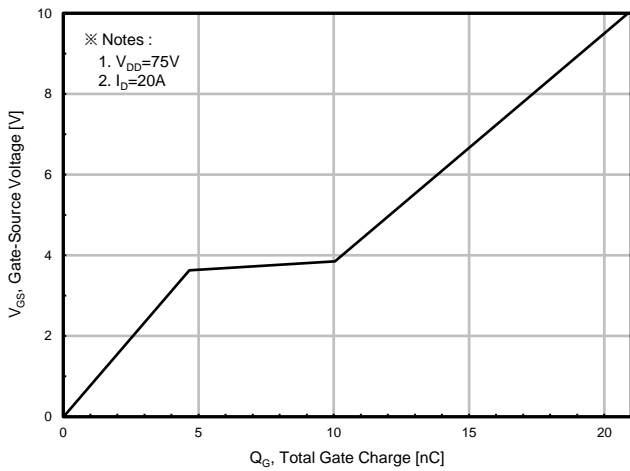


Fig. 7. Gate Charge

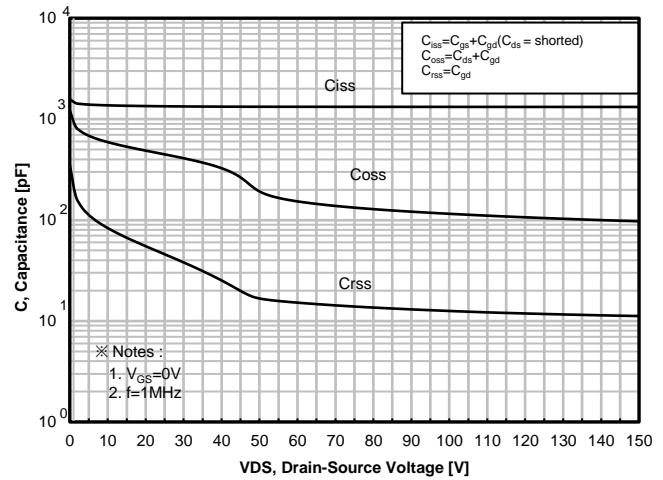


Fig. 8. Capacitance

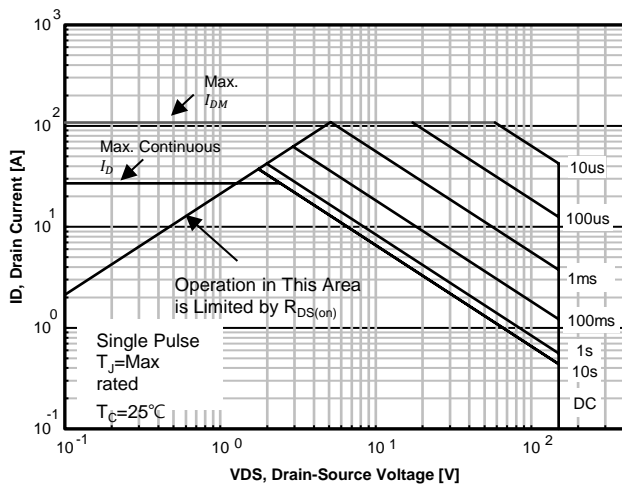


Fig. 9. Safe Operating Area, Junction-to-Ambient

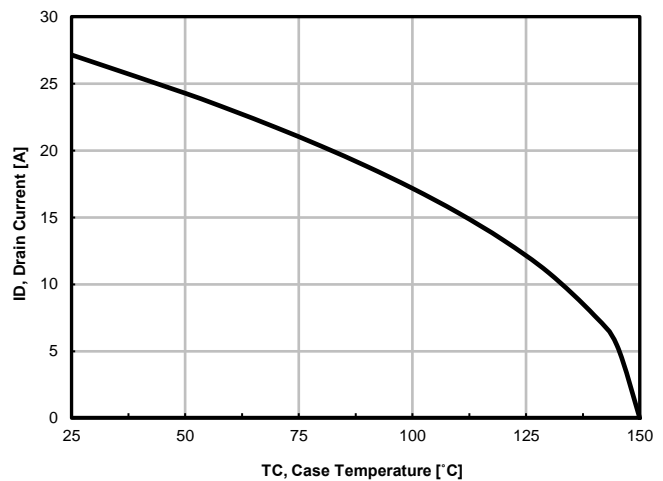


Fig. 10. Maximum Drain Current vs. Case Temperature

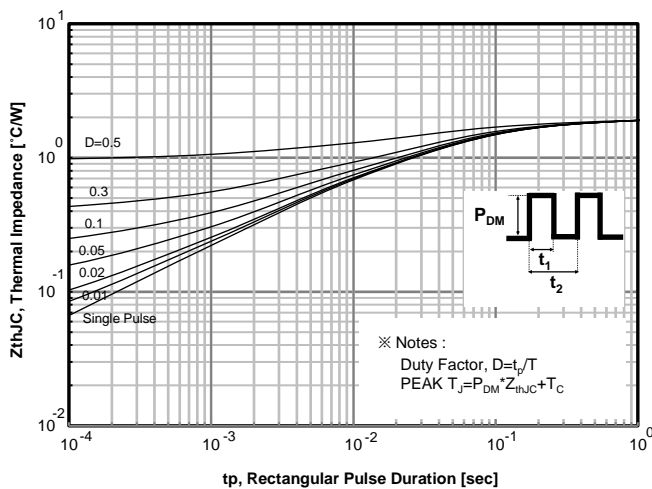
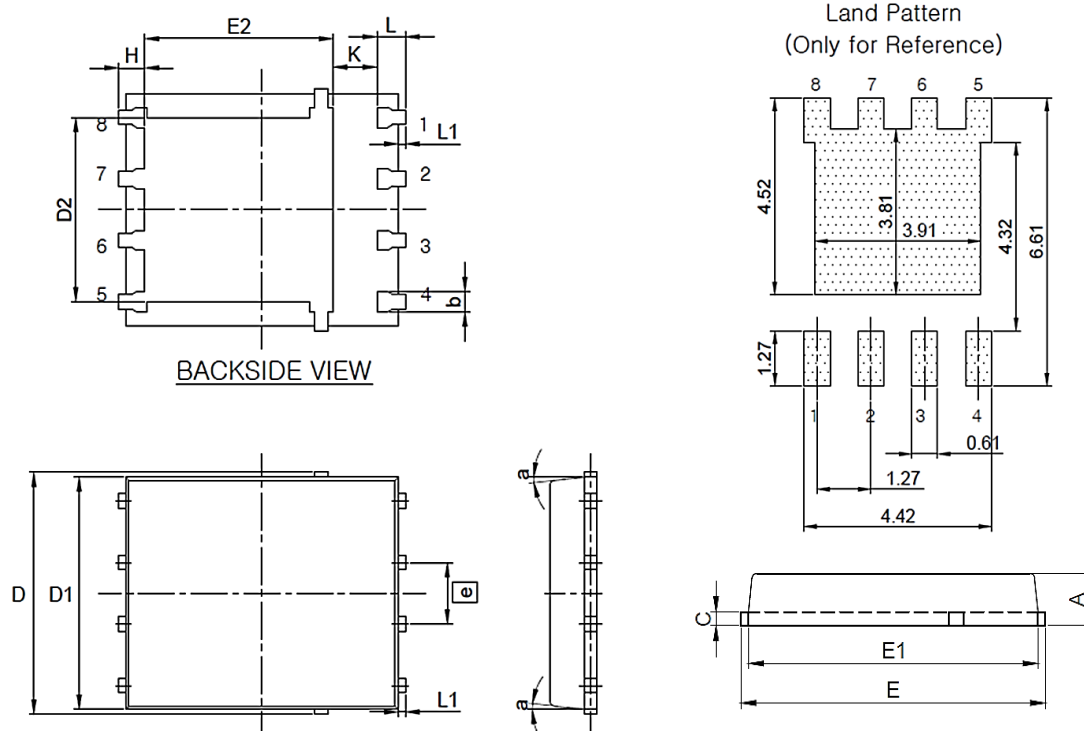


Fig. 11. Thermal Transient Impedance, Junction-to-Ambient

# Package information

PDFN56



Symbol	Dimension (mm)		
	Min.	Norm.	Max.
A	0.90	-	1.10
B	0.33	-	0.51
C	0.20	-	0.34
D	4.50	-	5.30
D1	4.50	-	5.10
D2	3.61	-	4.22
E	5.90	-	6.30
E1	5.50	-	6.10
E2	3.38	-	4.30
e	1.27 BSC		
H	0.41	-	0.71
K	0.20	-	-
L	0.51	-	0.71
L1	0.06	-	0.20
a	0°	-	12°


\* Note : Package body size, length and width do not include mold flash, protrusions and gate burrs.

## Notes

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**DISCLAIMER :**

The Products are not designed for use in hostile environments, including, without limitation, aircraft, nuclear power generation, medical appliances, and devices or systems in which malfunction of any Product can reasonably be expected to result in a personal injury. Seller's customers using or selling Seller's products for use in such applications do so at their own risk and agree to fully defend and indemnify Seller.

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